

GP2302

20V N-Channel MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)MAX}	I _D
201/	45mΩ@4.5V	2.1A
20V	60mΩ@2.5V	2.1A

Feature

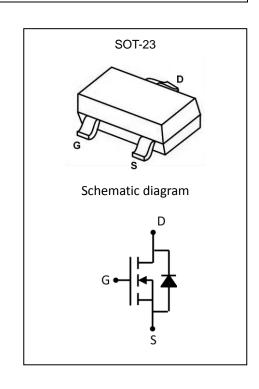
- TrenchFET Power MOSFET
- Excellent R_{DS(on)} and Low Gate Charge

Application

- DC/DC Converter
- Load Switch for Portable Devices
- Battery Switch

MARKING:





ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	20	V
Gate-Source Voltage	V_{GS}	±8	V
Continuous Drain Current	I _D	2.1	А
Plused Drain Current	I _{DM}	10	А
Continuous Source-Drain Current(Diode Conduction)	Is	0.6	А
Power Dissipation	P _D	0.35	W
Thermal Resistance from Junction to Ambient	R _{θJA}	357	°C/W
Junction Temperature	TJ	150	$^{\circ}\!\mathbb{C}$
Storage Temperature	T _{STG}	-55~ +150	℃



MOSFET ELECTRICAL CHARACTERISTICS(T_a=25℃ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Туре	Max	Unit
Static Characteristics			•			
Drain-source breakdown voltage	V _{(BR)DSS}	$V_{GS} = 0V, I_D = 250\mu A$	0V, I _D =250μA 20			V
Zero gate voltage drain current	I _{DSS}	$V_{DS} = 20V, V_{GS} = 0V$			1	μΑ
Gate-body leakage current	I _{GSS}	$V_{GS} = \pm 8V$, $V_{DS} = 0V$			±0.1	μΑ
Gate threshold voltage	$V_{GS(th)}$	V _{DS} =V _{GS} , I _D =250μA	0.6	0.9	1.2	V
Drain-source on-resistance ^a	В	V _{GS} =4.5V, I _D =3.6A		32	45	0
Drain-source on-resistance	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	mΩ				
Forward tranconductance ^a	g FS	V _{DS} =5V, I _D =3.6A	8			S
Dynamic characteristics			•			
Input Capacitance ^b	C _{iss}			260		pF
Output Capacitance ^b	C _{oss}	$V_{DS} = 10V, V_{GS} = 0V, f = 1MHz$		48		pF
Reverse Transfer Capacitance ^b	C _{rss}	_		27		pF
Total gate charge	Qg			2.9	5	nC
Gate-source charge	Q _{gs}	V _{DS} =10V,V _{GS} =4.5V,I _D =3.0A		0.4		nC
Gate-drain charge	Q_{gd}			0.6		nC
Switching Characteristics ^b						
Turn-on delay time	t _{d(on)}			2.5		ns
Turn-on rise time	t _r	V_{DD} =10V, R_L =3.3 Ω ,)V, R _L =3.3Ω,			ns
Turn-off delay time	t _{d(off)}	V_{GEN} =4.5V,Rg=6 Ω		21		ns
Turn-off fall time	tf			3		ns
Source-Drain Diode characteristics						
Diode Forward voltage	V _{DS}	V _{GS} =0V, I _S =0.94A		0.7	1.2	V

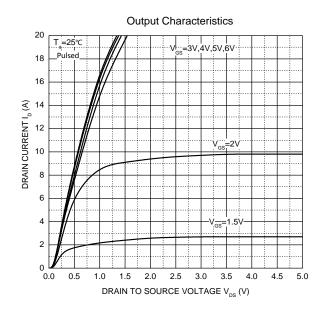
Notes:

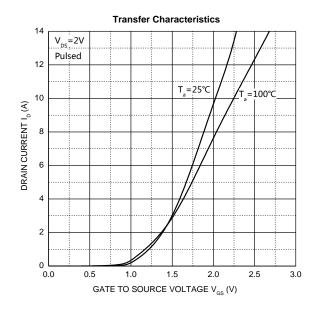
a. Pulse Test : Pulse width≤300µs, duty cycle ≤2%.

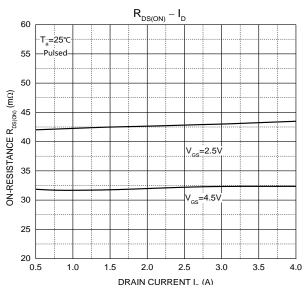
b. These parameters have no way to verify.

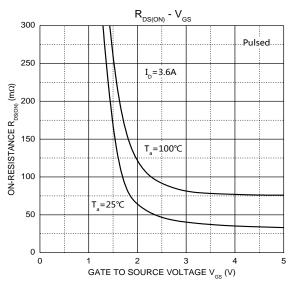


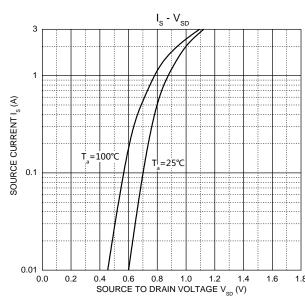
Typical Electrical and Thermal Characteristics

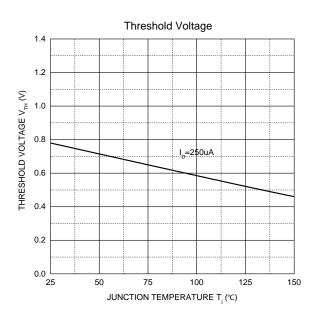






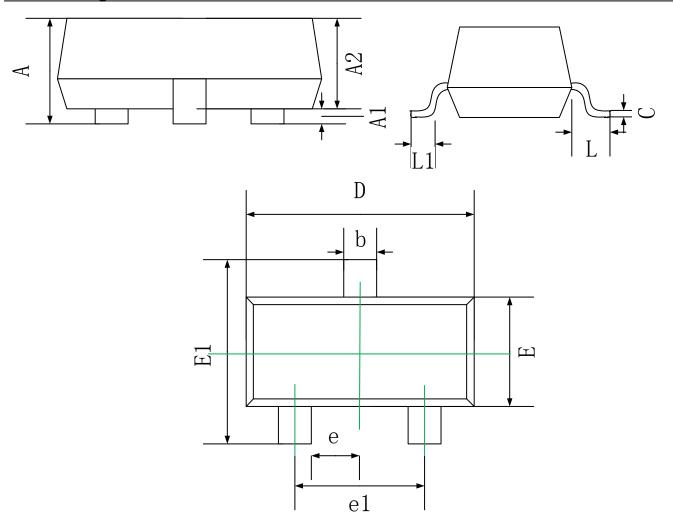








SOT-23 Package Information

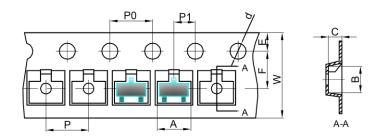


Cumhal	Dimensions	In Millimeters				
Symbol	Min.	Max.				
Α	0.90	1.15				
A1	0.00	0.10				
A2	0.90	1.05				
b	0.30	0.50				
С	0.08	0.15				
D	2.80	3.00				
E	1.20	1.40				
E1	2.25	2.55				
е	0.95 REF.					
e1	1.80	2.00				
L	0.55 REF.					
L1	0.30	0.50				



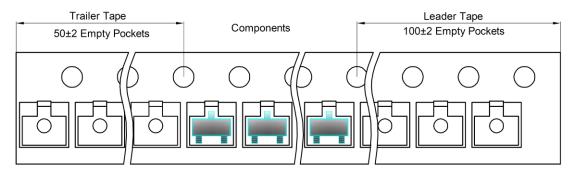
SOT-23 Tape and reel

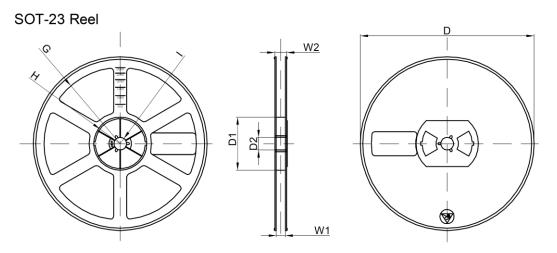
SOT-23 Embossed Carrier Tape



Dimensions are in millimeter									
Pkg type A B C d E F P0 P P1 W								W	
SOT-23									8.00

SOT-23 Tape Leader and Trailer





Dimensions are in millimeter								
Reel Option D D1 D2 G H I W1 W2								W2
7"Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	30,000 pcs	203×203×195	120,000 pcs	438×438×220	